



SOT-23 Plastic-Encapsulate MOSFETS

CJ2307 P-Channel 30-V(D-S) MOSFET

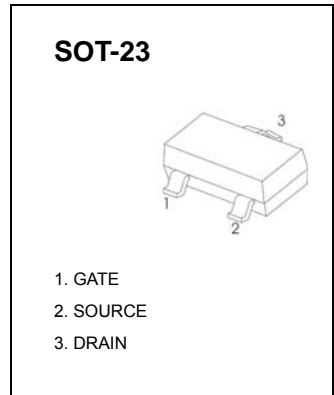
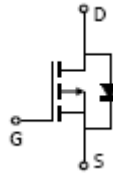
FEATURE

TrenchFET Power MOSFET

APPLICATIONS

Load Switch for Portable Devices

MARKING: S7



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^{a,b}	I_D	-2.7	A
Continuous Source-Drain Current ^{a,b}	I_S	-0.91	
Power Dissipation ^{a,b}	P_D	1.1	W
Thermal Resistance from Junction to Ambient ($t \leq 5s$)	$R_{\theta JA}$	114	$^{\circ}\text{C}/\text{W}$
Operating Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

Electrical characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1		-3	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -30V, V_{GS} = 0V, T_J = 55^{\circ}\text{C}$			-10	
Drain-Source On-State Resistance ^c	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -2.5A$		0.110	0.138	Ω
		$V_{GS} = -10V, I_D = -3.5A$		0.073	0.088	
Forward Transconductance ^c	g_{fs}	$V_{DS} = -10V, I_D = -3.5A$		7		S
Dynamic^d						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1\text{MHz}$		340		pF
Output Capacitance	C_{oss}			67		
Reverse Transfer Capacitance	C_{rss}			51		
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -2.5A$		4.1	6.2	nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.8		
Gate Resistance	R_g	$f = 1\text{MHz}$		10		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15V, R_L = 15\Omega, I_D = -1A, V_{GEN} = -4.5V, R_g = 1\Omega$		40	60	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			20	40	
Fall Time	t_f			17	30	
Drain-source Body diode characteristics						
Body Diode Voltage	V_{SD}	$I_S = -0.75A, V_{GS} = 0$		-0.8	-1.2	V

Notes:

- $t = 5s$.
- Surface mounted on 1" x 1" FR4 board.
- Pulse Test : Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Typical Characteristics

CJ2307

